

- 2. Problem 2 is shown on the next page (out of order).
- 3. (4 pts) Why is a sinusoidal waveform NOT really a signal?
- 4. (4 pts) If you built the circuit at right in the lab, with a real LM741, what should you expect to measure at the output?





5. (13 pts) The circuit at right is operated so that the $\ensuremath{v_{\text{DS}}}$ is small.

MOSFET characteristics: $k' n \cdot \frac{W}{L} = K = 2 \cdot \frac{mA}{V^2}$ $V_t = 1.5 \cdot V$

a) Find the gain (v_o/v_{in}) of this circuit if: V $_G := 4 \cdot V$

b) Find a general expression for the gain as a function of R_1 , R_2 , V_G , and the characteristics of the MOSFET.

2. (22 pts)

a) Assume the op amp is ideal (doesn't even clip). The input waveform (v_S) is as shown. Accurately draw the output voltage (v_o) you expect to see. Draw the output on the graph provided and label the vertical axis.

b) If you actually make the circuit with an LM741, the output waveform may be a little different. Accurately show how the real output differs from the ideal. label any newly drawn lines "real".

Label important voltages OR times so that each important point on the waveform is clear.

Note: Some of the characteristics of this op amp are unimportant and won't significantly change the output. You may neglect any characteristics which will affect the output by less than 5% (you don't need to prove your assumptions). $R_2 = 180 \cdot k\Omega$



LM741 Op amp Characteristics

Differential gain:	$A_{V} = 100000$
Unity-gain bandwidth:	$f_T = 2 \cdot MHz$
Output swing limits:	within 2 V of supplies L+ = V+ - 2V L- = V- + 2V
Slew rate:	$SR := 1 \cdot \frac{V}{\mu s}$
Input bias current:	$I_B := -80 \cdot nA$

6. (14 pts) All the MOSFETS shown are built on the same IC, using the same process. The only differences between them are their physical dimensions and the k'_n , k'_p difference.

All transistors are operating in saturation.

a) Find I

a) Find I₂ b) Find I₄
c) Find I₅ d) K₁ =
$$2 \cdot \frac{mA}{V^2} = k' p \cdot \frac{W_1}{L_1}$$

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ECE 2100 Final given Spring 2002 p3 $V_t = k'_n \cdot \frac{W}{L} = R_D$ and V_{DD}

7. (8 pts) Assuming you know

Derive an expression for I_D or show the equation that you' d have to solve in order to find_D. If you leave your answer as an equation, it must be in a polynomial form for easy solution.

I suggest that you take an equation you already have and modify it to fit this circuit. Deriving it from scratch will take too long for 8 points.



VDD

RD

D

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9. (22 pts) A voltage waveform (dotted line) is applied to the circuits shown. Accurately draw the output waveform (v_0) you expect to see. The characteristic curve for the 2.1-V silicon zener diode is also shown. Label important times and voltage levels.



10. (8pts)The MOSFETs in the circuit shown are matched and both have: $|V_t| = 3 \cdot V$ Find V_{IL} , V_{IH} , and the noise margins.



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11. (14pts) Assume the depletion-type MOSFET shown is operating in saturation.

a) Find
$$K = k' \frac{W}{L}$$
 $V_t = -3 \cdot V$

b) I want the to stay in saturation. What is the biggest R_D that I can use?

12. Do you want your grade and scores posted on my door and on the internet? Yes No (Circle one)

 $R_{G} = 5 \cdot M\Omega$

 $R_{\rm S} = 200 \cdot \Omega$

If your answer is yes, then provide some sort of alias or password: _

The grades will be posted on my door in alphabetical order under the alias that you provide here. I will not post grades under your real name. The internet version will be an excel spreadsheet which you can download. Both will show all your homework, lab, and exam scores.



10. 5.25V, 6.75V, 5.25V 11.a) 2.5mA/V² b) 1.8kΩ

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